

SANYO	No.2456	2SA1436
		PNP Epitaxial Planar Silicon Transistor

High- h_{FE} , AF Amp Applications

Applications

- . AF amp, various drivers, muting circuit

Features

- . Adoption of MBIT process
- . High DC current gain ($h_{FE}=500$ to 1200)
- . Large current capacity
- . Low collector to emitter saturation voltage ($V_{CE(sat)}=0.5V$ max)
- . High V_{EBO} ($V_{EBO} \geq 15V$)

Absolute Maximum Ratings at $T_a=25^\circ C$

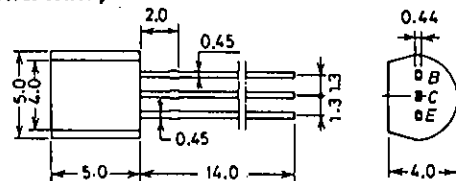
			unit
Collector to Base Voltage	V_{CBO}	-60	V
Collector to Emitter Voltage	V_{CEO}	-50	V
Emitter to Base Voltage	V_{EBO}	-15	V
Collector Current	I_C	-200	mA
Collector Current(Pulse)	I_{CP}	-300	mA
Collector Dissipation	P_C	600	mW
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to +150	$^\circ C$

Electrical Characteristics at $T_a=25^\circ C$

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=-40V, I_E=0$			-0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=-10V, I_C=0$			-0.1	μA
DC Current Gain	$h_{FE}(1)$	$V_{CE}=-5V, I_C=-10mA$	500	800	1200	
	$h_{FE}(2)$	$V_{CE}=-5V, I_C=-100mA$	200			
Gain-Bandwidth Product	f_T	$V_{CE}=-10V, I_C=-10mA$		100		MHz
Output Capacitance	c_{ob}	$V_{CB}=-10V, f=1MHz$		7.5		pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C=-100mA, I_B=-2mA$	-0.2	-0.5		V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C=-100mA, I_B=-2mA$	-0.75	-1.1		V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C=-10\mu A, I_E=0$	-60			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C=-1mA, R_{BE}=\infty$	-50			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E=-10\mu A, I_C=0$	-15			V

Package Dimensions 2003A

(unit: mm)

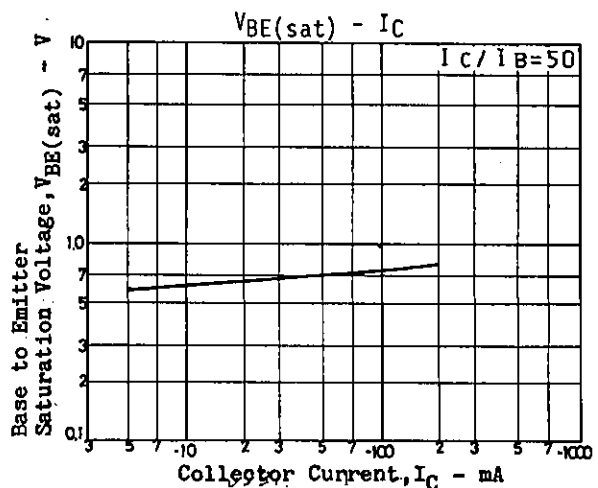
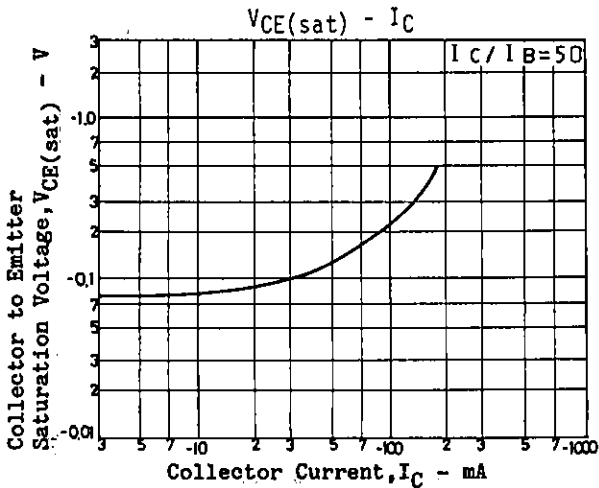
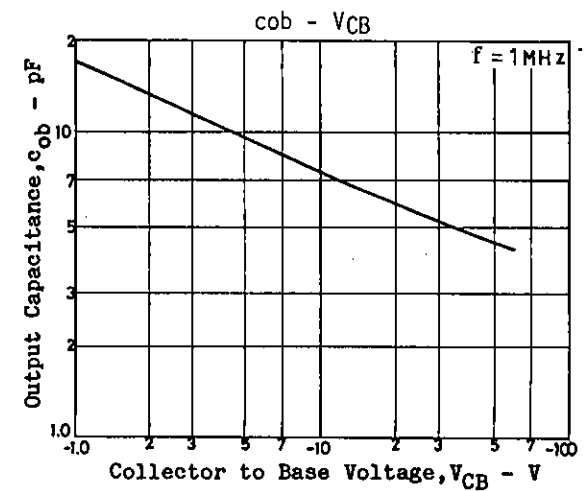
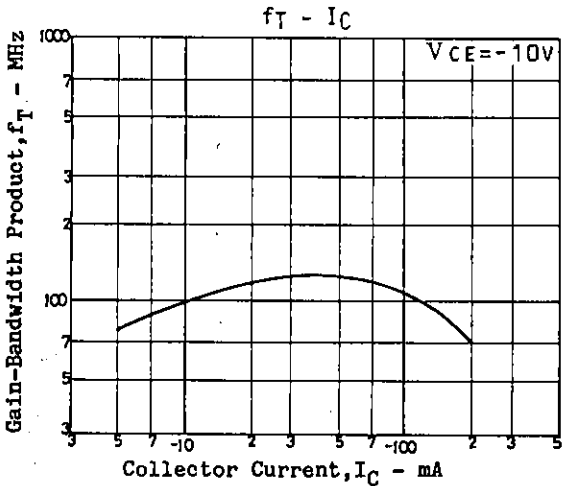
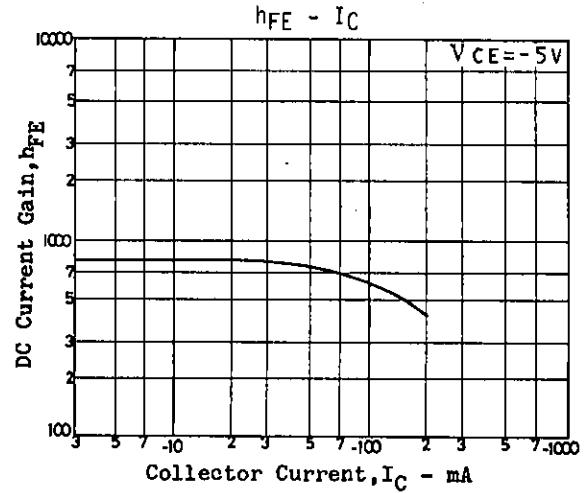
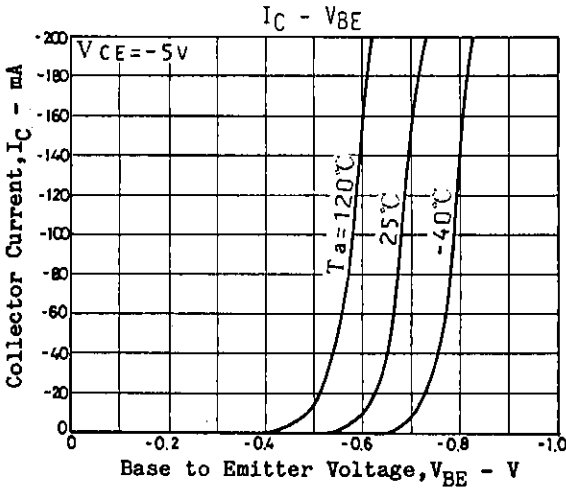
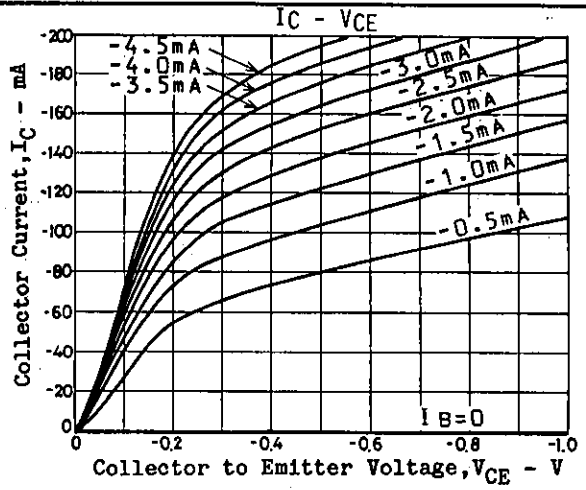
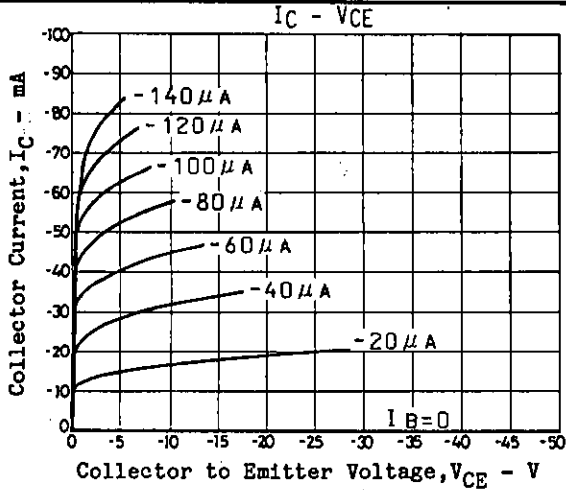


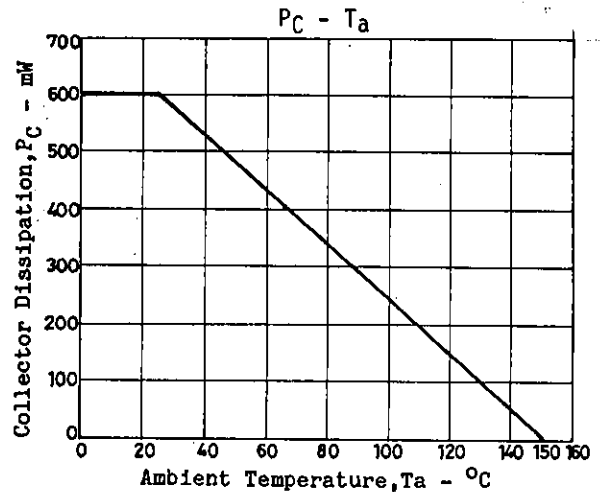
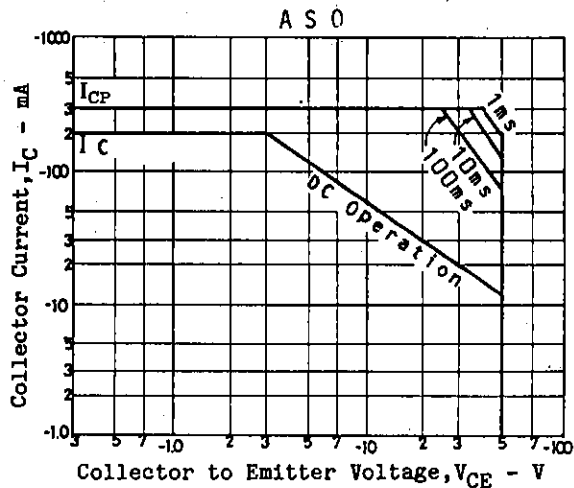
JEDEC: TO-92
EIAJ: SC-43
SANYO: NP

B. Base
C. Collector
E. Emitter

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